

Vishay Siliconix

Low Capacitance, Low Charge Injection, 4- / 8-Channel, Triple SPDT, ± 5 V / 12 V / 5 V / 3 V Analog Multiplexers

DESCRIPTION

The DG4051E, DG4052E, and DG4053E are high precision CMOS analog multiplexers. The DG4051E is an 8-channel multiplexer, the DG4052E is a dual 4-channel multiplexer, and the DG4053E is a triple 2-channel multiplexer or triple SPDT.

The DG4051E, DG4052E, and DG4053E feature low leakage, parasitic capacitance, and low charge injection of 0.3 pC over the full voltage range. These devices are ideal for high precision signal switching and multiplexing.

Designed to operate from a 3 V to 16 V single supply or from a \pm 3 V to \pm 8 V dual supplies, the DG4051E, DG4052E, and DG4053E are fully specified at 3 V, 5 V, 12 V and \pm 5 V. All control logic inputs have guaranteed 2 V logic high limit when operating from 5 V or \pm 5 V supplies and 1.4 V when operating from a 3 V supply.

All switches conduct equally well in both directions, offering rail to rail analog signal switching and can be used both as multiplexers as well as de-multiplexers.

The DG4051E, DG4052E, and DG4053E operating temperature is specified from -40 °C to +125 °C and are available in 16 pin TSSOP and the ultra compact 1.8 mm x 2.6 mm miniQFN16 packages.

BENEFITS

- Wide operation voltage range
- Low charge injection
- Low parasitic capacitance
- · Compact package option

FEATURES

 3 V to 16 V single supply or ± 3 to ± 8 V dual supply operation



RoHS

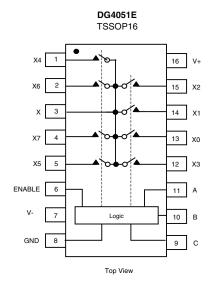
 Low parasitic capacitance: C_{D(ON)}: 8.5 pF / typ. (DG4053E) C_{S(OFF)}: 2.0 pF / typ. (DG4053E)

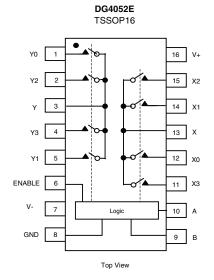
- Less than 0.3 pC charge injection over the full signal swing range
- Low leakage: < 50 pA, typ.
- Fast switching ton: 35 ns, typ.
- 3 V logic compatible for control
- Bi-directional rail to rail signal switching
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

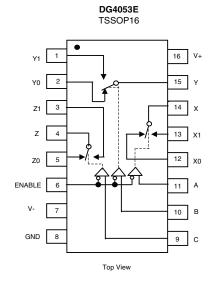
APPLICATIONS

- Automatic test equipment
- · Process control and automation
- · Data acquisition systems
- · Meters and instruments
- Medical and healthcare systems
- · Communication systems
- Audio and video signal routing
- Relay replacement
- Battery powered systems

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION







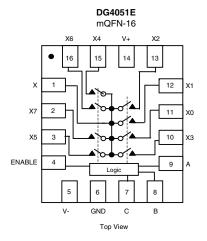
ENABLE = LO, all switches are controlled by addr pins ENABLE = HI, all switches are off.

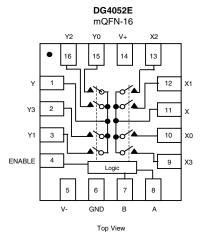
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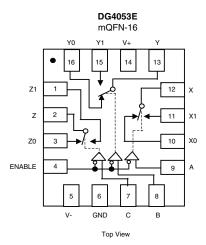


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FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION









 $\begin{array}{ll} \text{Device Marking: } \underline{Fxx} \text{ for DG4051E} \\ \text{(miniQFN16)} & \underline{G}xx \text{ for DG4052E} \\ \underline{H}xx \text{ for DG4053E} \\ xx = \text{Date/Lot Traceability Code} \end{array}$

TRUTH 1	TABLE							
ENABLE		SELECT INPUTS		ON SWITCHES				
INPUT	С	В	Α	DG4051E	DG4052E	DG4053E		
Н	Х	Х	Х	All switches open	All switches open	All switches open		
L	L	L	L	X to X0	X to X0, Y to Y0	X to X0, Y to Y0, Z to Z0		
L	L	L	Н	X to X1	X to X1, Y to Y1	X to X1, Y to Y0, Z to Z0		
L	L	Н	L	X to X2	X to X2, Y to Y2	X to X0, Y to Y1, Z to Z0		
L	L	Н	Н	X to X3	X to X3, Y to Y3	X to X1, Y to Y1, Z to Z0		
L	Н	L	L	X to X4	X to X0, Y to Y0	X to X0, Y to Y0, Z to Z1		
L	Н	L	Н	X to X5	X to X1, Y to Y1	X to X1, Y to Y0, Z to Z1		
L	Н	Н	L	X to X6	X to X2, Y to Y2	X to X0, Y to Y1, Z to Z1		
L	Н	Н	Н	X to X7	X to X3, Y to Y3	X to X1, Y to Y1, Z to Z1		

ORDERING INFORM	IATION			
TEMPERATURE RANGE	CONFIGURATION	PACKAGE PART NUMBER MIN. ORD		MIN. ORDER / PACKAGING QUANTITY
		16-pin TSSOP	DG4051EEQ-T1-GE3	Tape and reel 3000 units
	DG4051E	16-pin SOIC	DG4051EEY-T1-GE3	Tape and reel 2500 units
		16-pin miniQFN	DG4051EEN-T1-GE4	Tape and reel 3000 units
40.00 1 405.00 2		16-pin TSSOP	DG4052EEQ-T1-GE3	Tape and reel 3000 units
-40 °C to +125 °C ^a Lead (Pb)-Free	DG4052E	16-pin SOIC	DG4052EEY-T1-GE3	Tape and reel 2500 units
Load (i b) i ico		16-pin miniQFN	DG4052EEN-T1-GE4	Tape and reel 3000 units
		16-pin TSSOP	DG4053EEQ-T1-GE3	Tape and reel 3000 units
	DG4053E	16-pin SOIC	DG4053EEY-T1-GE3	Tape and reel 2500 units
		16-pin miniQFN	DG4053EEN-T1-GE4	Tape and reel 3000 units

Note

a. -40 °C to +85 °C datasheet limits apply.

Vishay Siliconix

ABSOLUTE MAXIMUM RATING	S (T _A = 25 °C, unless other	vise noted)	
PARAMETER		LIMIT	UNIT
V+ to V-		-0.3 to +18	
GND to V-		-18	\Box \lor
Digital Inputs ^a , V _S , V _D	(V-) - 0.3 to (V+) + 0.3 or 30 mA, whichever occurs first		
Continuous Current (any terminal)		30	mA
Peak Current, S or D (pulsed 1 ms, 10 % du	ty cycle)	100	IIIA
Storage Temperature		-65 to +150	°C
	16-pin TSSOP ^c	450	
Power Dissipation ^b	16-pin miniQFN ^{d, f}	525	mW
	16-pin narrow SOIC ^e	640	
	16-pin TSSOP ^c	178	
Thermal Resistance ^b	16-pin miniQFN ^{d, f}	152	°C/W
	16-pin narrow SOIC e	125	7
ESD Human Body Model (HBM); per ANSI /	ESDA / JEDEC® JS-001	2500	V
Latch Up Current, per JESD78D		400	mA

Notes

- a. Signals on SX, DX, or INX exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 5.6 mW/°C above 70 °C.
- d. Derate 6.6 mW/°C above 70 °C.
- e. Derate 8.0 mW/°C above 70 °C.
- f. Manual soldering with iron is not recommended for leadless components. The miniQFN-16 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper lip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS	S FOR D	UAL SUPPLIES								
		TEST CONDITIONS			-40 °C to	+125 °C	-40 °C t	o +85 °C		
PARAMETER	SYMBOL	UNLESS OTHERWISE SPECIFIED V+ = 5 V, V- = -5 V V _{IN(A, B, C, and enable)} = 2 V, 0.8 V a	TEMP. b	TYP. °	MIN. d	MAX. d	MIN. d	MAX. d	UNIT	
Analog Switch										
Analog Signal Range e	V _{ANALOG}		Full	-	-5	5	-5	5	V	
On-Resistance	R _{ON}	Is = 1 mA. V _D = -3 V. 0 V. 3 V	Room	68	-	78	-	78		
On-nesistance		$I_S = I IIIA, V_D = -3 V, 0 V, 3 V$	Full	-	-	106	-	97		
On-Resistance Match	ΔR_{ON}	$I_S = 1 \text{ mA}, V_D = \pm 3 \text{ V}$	Room	0.91	-	6	-	6	Ω	
On-nesistance Match	ΔηΟΝ	$I_S = I IIIA, V_D = \pm 3 V$	Full	-	-	6	-	6	5.2	
On-Resistance	D	Is = 1 mA. V _D = -3 V. 0 V. 3 V	Room	10	-	17	-	17		
Flatness	R _{FLATNESS}	IS = 1 IIIA, VD = -3 V, 0 V, 3 V	Full	-	-	20	-	19		
	I _{S(off)}		Room	± 0.05	-1	1	-1	1		
Switch Off		V+ = 5.5 V, V- = -5.5 V,	Full	-	-50	50	-5	5	nA	
Leakage Current	1	$V_D = \pm 4.5 \text{ V}, V_S = \mp 4.5 \text{ V}$	Room	± 0.05	-1	1	-1	1		
	I _{D(off)}		Full	-	-50	50	-5	5		
Channel On	1	V+ = 5.5 V, V- = -5.5 V,	Room	± 0.05	-1	1	-1	1		
Leakage Current	I _{D(on)}	$V_S = V_D = \pm 4.5 \text{ V}$	Full	-	-50	50	-5	5		
Digital Control										
Input Current, V _{IN} Low	I _{IL}	$V_{IN(A,\ B,\ C,\ and\ enable)}$ under test = 0.6 V	Full	0.02	-1	1	-1	1		
Input Current, V _{IN} High	I _{IH}	V _{IN(A, B, C, and enable)} under test = 2 V	Full	0.02	-1	1	-1	1	μA	
Input Capacitance e	C _{IN}	f = 1 MHz	Room	3.4	-	-	-	1	pF	



		TEST CONDIT	-			-40 °C to	+125 °C	-40 °C to +85 °C		
PARAMETER	SYMBOL	V+ = 5 V, V- = -5 V		TEMP. b	TYP. c	MIN. d	MAX. d	MIN. d	MAX. d	UNIT
		$V_{IN(A, B, C, and enable)} = 2 V, 0.8 V^a$								
Dynamic Characterist	ics									
			f = 100 kHz	Room	-106	-	-	-	-	
Off Isolation e	OIRR		f = 10 MHz	Room	-68	-	-	-	-	
		$R_L = 50 \Omega$, $C_L = 1 pF$	f = 100 MHz	Room	-49	-	ı	-	ı	dB
01 11 01 1		nt = 30 32, Ot = 1 pr	f = 100 kHz	Room	-105	-	ı	-	ı	ub
Channel-to-Channel Crosstalk e	X_{TALK}		f = 10 MHz	Room	-62	-	-	-	-	
O O O O O O O O O O O O O O O O O O O			f = 100 MHz	Room	-51	-	-	-	-	
			DG4051E	Room	308	-	-	-	-	
Bandwidth, 3 dB	BW	$R_L = 50 \Omega$	DG4052E	Room	353	-	-	-	-	MHz
			DG4053E	Room	930	-	-	-	-	
Transition Time			Room 72		72	-	112	-	112	
Transition Time	t _{TRANS}			Full	-	-	139	-	131	
Facility of Oak			Room	35	-	75	-	75		
Enable Turn-On Time	t _{ON}	$R_L = 300 \Omega, C_L = 100 \Omega$	= 35 pF	Full	-	-	86	-	80	
5 II 5 0" F		see Fig. 1, 2	2, 3	Room	48	-	88	-	88	ns
Enable Turn-Off Time	t _{OFF}		Full	-	-	97	-	95		
Break-Before-Make				Room	-	1	-	1	-	
Time Delay	t _D					-	-	-	-	
Charge Injection e	Q	$V_a = 0 \text{ V}, R_a = 0 \Omega,$	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 1 \text{ nF}$		0.38	-	-	-	-	рС
	C _{S(off)}		DG4051E	Room	2.2	-	-	-	-	-
Source Off		f = 1 MHz	DG4052E	Room	2.1	-	-	-	-	
Capacitance e			DG4053E	Room	2	-	-	-	-	
			DG4051E	Room	9.2	-	-	-	-	
Drain Off	C _{D(off)}	f = 1 MHz	DG4052E	Room	4.8	-	-	-	-	pF
Capacitance e	= (0)		DG4053E	Room	3.1	-	-	-	-	
			DG4051E	Room	14.9	-	-	-	-	
Channel On	C _{D(on)}	f = 1 MHz	DG4052E	Room	10	-	-	-	-	
Capacitance e	2(0.1)		DG4053E	Room	8.5	-	-	-	-	
Total Harmonic Distortion ^e	THD	Signal = 5 V _I 20 Hz to 20 kHz, F		Room	0.065	-	-	-	-	%
Power Supplies										
D 0 10 1				Room	0.05	-	1	_	1	
Power Supply Current	I+			Full	-	-	10	-	10	1
Negative Supply		V+ = 5 V, V- =	5 V	Room	-0.05	-1	-	-1	-	1
Current	I-	V+=5 V, V-=-5 V $V_{IN(A, B, C, and enable)} = 0 V or 5 V$		Full	-	-10	-	-10	-	μA
		Intringuity, 5, 5, and shadely		Room	-0.05	-1	-	-1	-	1
Ground Current	I _{GND}			Full	-	-10	_	-10	_	1



		TEST CONDI				-40 °C to +125 °C		-40 °C to +85 °C		
PARAMETER	SYMBOL	UNLESS OTHERWIS V+ = 12 V, V-		TEMP. b	TYP. c	MIN. d	MAX. d	MIN. d	MAX. d	UNI
		V _{IN(A, B, C, and enable)} =				IVIII 4.	WIAX.	IVIII V.	WAX.	
Analog Switch										
Analog Signal Range e	V _{ANALOG}			Full	-	0	12	0	12	V
On-Resistance	R _{ON}	$I_S = 1 \text{ mA}, V_D = 0.$	7 V 11 3 V	Room	85	-	103	-	103	
On-nesistance	TION	is = 1 ma, vp = 0.	7 V, 11.5 V	Full	-	-	133	-	125	
On-Resistance Match	ΔR_{ON}	$I_S = 1 \text{ mA}, V_D =$	- 11 3 V	Room	1.24	-	8	-	8	Ω
On-nesistance materi	ZHON	is – i iiia, vp –	- 11.5 V	Full	-	-	8	-	8	52
On-Resistance	R _{FLATNESS}	$I_S = 1 \text{ mA}, V_D = 0.$	7 V 11 3 V	Room	27	-	37	-	37	
Flatness	TIFLATNESS	is = 1 ma, v _D = 0.	7 V, 11.0 V	Full	-	-	44	-	43	
	la			Room	± 0.05	-1	1	-1	1	
Switch Off	I _{S(off)}	V+ = 13.2 V, V		Full	-	-50	50	-5	5	
Leakage Current	I	$V_D = 1 \text{ V} / 12.2 \text{ V}, V_S = 12.2 \text{ V} / 1 \text{ V}$		Room	± 0.05	-1	1	-1	1	nA
	I _{D(off)}			Full	-	-50	50	-5	5	II/A
Channel On	1	V+ = 13.2 V, V- = 0 V V _D = V _S = 1 V / 12.2 V		Room	± 0.05	-1	1	-1	1	
Leakage Current	I _{D(on)}			Full	-	-50	50	-5	5	
Digital Control										
Input Current, V _{IN} Low	ΙL	V _{IN(A, B, C, and enable)} under test = 0.8 V		Full	0.02	-1	1	-1	1	μА
Input Current, V _{IN} High	I _H	$V_{IN(A, B, C, and enable)}$ under test = 2 V		Full	0.02	-1	1	-1	1	μΑ
Dynamic Characterist	ics									
Transition Time			Room	43	-	83	-	83		
Transition Time	t _{TRANS}	TRANS		Full	-	-	95	-	90	
Facility of Carting				Room	22	-	62	-	62	
Enable Turn-On Time	t _{ON}	$R_L = 300 \Omega, C_L = 35 pF$ see Fig. 1, 2, 3		Full	-	-	71	-	67	ns
Facility Of Tax				Room	47	-	87	-	87	ns
Enable Turn-Off Time	t _{OFF}			Full	-	-	94	-	93	
Break-Before-Make				Room	25	1	-	1	-	
Time Delay	t _D			Full	-	-	-	-	-	
Charge Injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega$, C _L = 1 nF	Full	-	-	-	-	-	рС
Off Isolation e	OIRR	D 50.0.0	1 5 5	Room	-	-	-	-	-	
Channel-to-Channel Crosstalk ^e	X _{TALK}	$R_L = 50 \Omega, C_L$ f = 100 kH	= i pr Iz	Room	-	-	-	-	-	dB
			DG4051E	Room	-	-	-	-	-	
Source Off Capacitance ^e	C _{S(off)}	f = 1 MHz	DG4052E	Room	-	-	-	-	-	
Capacitance	, ,		DG4053E	Room	-	-	-	-	-	
			DG4051E	Room	-	-	-	-	-	
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz	DG4052E	Room	-	-	-	-	-	рF
Capacitance	. ,		DG4053E	Room	-	-	-	-	-	
			DG4051E	Room	-	-	-	-	-	
Channel On Capacitance ^e	C _{D(on)}	f = 1 MHz	DG4052E	Room	-	-	-	-	-	
Capacitance ⁹	(- /	DG4053E		Room	-	-	-	-	-	
Power Supplies										
Power Supply Coment	w Committee Committee			Room	0.05	-	1	-	1	
Power Supply Current	ly Current I+		Full	-	-	10	-	10		
Negative Supply	,	V			-0.05	-1	-	-1	-	
Current	I-	I- V _{IN(A, B, C, and enable)} = 0 V or 5 V		Full	-	-10	-	-10	-	μA
0 10 1	,			Room	-0.05	-1	-	-1	-	1
Ground Current	I_{GND}			Full	-	-10	-	-10	1	1



		TEST CONDI				-40 °C to +125 °C		-40 °C to +85 °C		
PARAMETER	SYMBOL	UNLESS OTHERWIS V+ = 5 V, V-		TEMP. b	TYP. c	MIN. d	MAX. d	MIN. d	MAX. d	UNI
		V _{IN(A, B, C, and enable)} =	= 2 V, 0.8 V ^a							
Analog Switch	1			1		ı	ı		T	
Analog Signal Range e	V _{ANALOG}			Full	-	0	5	0	5	V
On-Resistance	R _{ON}	$I_{S} = 1 \text{ mA}, V_{D} = 0$) V, 3.5 V	Room	125	-	147	-	147	
	0			Full	-	-	176	-	168	
On-Resistance Match	ΔR_{ON}	$I_S = 1 \text{ mA}, V_D = 1 \text{ mA}$	= 3.5 V	Room	1.3	-	8	-	8	Ω
				Full	-	-	8	-	8	
On-Resistance Flatness	R _{FLATNESS}	$I_S = 1 \text{ mA}, V_D =$	0 V, 3 V	Room Full	21	-	31	-	31	
Tiatriess					- 0.02	- -1	25 1	- -1	29	
	I _{S(off)}			Room	± 0.03				1	
Switch Off Leakage Current	` ,	$V_{+} = 5.5 V, V_{-}$ $V_{D} = 1 V / 4.5 V, V_{S}$		Full	-	-50	50	-5	5	
Leakage Current	I _{D(off)}	v _D = 1 v / 4.3 v, v _S	= 4.5 V / T V	Room	± 0.03	-1	1	-1	1	nA
	` ,			Full	-	-50	50	-5	5	
Channel On	I _{D(on)}	V+ = 5.5 V, V- = 0 V $V_D = V_S = 1 V / 4.5 V$		Room	± 0.03	-1	1	-1	1 -	
Leakage Current	(* ,	v _D = v _S = 1 v	7 4.5 V	Full	_	-50	50	-5	5	
Digital Control	1 1			1	1	ı	ı		ı	
Input Current, V _{IN} Low	ΙL	V _{IN(A, B, C, and enable)} under test = 0.6 V		Full	0.02	-1	1	-1	1	μΑ
Input Current, V _{IN} High	I _H	$V_{IN(A, B, C, and enable)}$ under test = 2 V		Full	0.02	-1	1	-1	1	ļ
Dynamic Characterist	ics									
Transition Time	t _{TRANS}		Room	95	-	135	-	135		
Transition fille	TRANS			Full	-	-	169	-	148	
Enable Turn-On Time	+				56	-	96	-	96	
Lilable fulli-Off fillie	t _{ON}	$R_L = 300 \Omega, C_L$	= 35 pF	Full	-	-	117	-	107	ns
Enable Turn-Off Time	to	see Fig. 1,	2, 3	Room	55	-	95	-	95	113
Lilable fulli-Oil fillie	t _{OFF}			Full	-	-	110	-	103	
Break-Before-Make	t _D			Room	-	12	-	12	-	
Time Delay	ιD			Full	-	-	-	-	-	
Charge Injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega$, C _L = 1 nF	Full	0.32	-	-	-	-	рС
Off Isolation e	OIRR	$R_L = 50 \Omega, C_L$	– 1 nF	Room	-86	-	-	-	-	
Channel-to-Channel Crosstalk ^e	X _{TALK}	f = 100 kł	- i pi Iz	Room	-105	-	-	-	-	dB
			DG4051E	Room	2.4	-	-	-	-	
Source Off Capacitance e	C _{S(off)}	f = 1 MHz	DG4052E	Room	2.4	-	-	-	-	
Capacitarice			DG4053E	Room	2.3	-	-	-	-	
			DG4051E	Room	10.1	-	-	-	=.	
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz	DG4052E	Room	5.3	-	-	-	-	рF
Capacitarice			DG4053E	Room	3.4	-	-	-	-	
			DG4051E	Room	15.9	-	-	-	-	
Channel On Capacitance ^e	C _{D(on)}	f = 1 MHz	DG4052E	Room	10.6	-	-	-	-	1
Оараспапсе			DG4053E	Room	8.9	-	-	-	-	
Power Supplies										
Power Supply Current	L			Room	0.05	-	1	-	1	
- ower ouppry ourrent	Current I+		Full		-	10	-	10		
Negative Supply	ı	V	, , , , , , , , , , , , , , , , , , ,		-0.05	-1	-	-1	-	
Current	I-	$V_{IN(A,\;B,\;C,\;and\;enable)}$	= U V Or 5 V	Full	-	-10	-	-10	-	μA
Cround Comment				Room	-0.05	-1		-1	-	
Ground Current	I_{GND}			Full	-	-10	-	-10	_	1

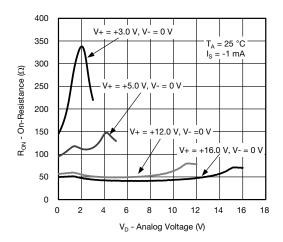


		TEST CONDIT	TIONS			-40 °C to	o +125 °C	-40 °C t	o +85 °C	
PARAMETER	SYMBOL	UNLESS OTHERWIS		TEMP. b	TYP. °	_				UNI
		$V+=3~V,~V-=V_{IN(A,~B,~C,~and~enable)}=$				MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch	1	IN(A, B, O, and enable)	,			l	l	1	L	
Analog Signal Range e	V _{ANALOG}			Full	-	0	3	0	3	V
2 2				Room	221	-	_	-	-	_
On-Resistance	R _{ON}	$I_S = 1 \text{ mA, } V_D =$	= 1.5 V	Full	-	-	-	-	-	Ω
				Room	± 0.02	-1	1	-1	1	
Switch Off	I _{S(off)}	V+ = 3.3 V, V-	= 0 V	Full	-	-50	50	-5	5	
Leakage Current		$V_D = 0.3 \text{ V} / 3 \text{ V}, V_S = 0.3 \text{ V}$		Room	± 0.02	-1	1	-1	1	
	I _{D(off)}			Full	-	-50	50	-5	5	n/
Channel On		V+ = 3.3 V. V-	V+ = 3.3 V, V- = 0 V		± 0.02	-1	1	-1	1	
Leakage Current	I _{D(on)}	$V_D = V_S = 0.3 \text{ V} / 3 \text{ V}$		Full	-	-50	50	-5	5	
Digital Control	I					L	l		L	<u> </u>
Input Current, V _{IN} Low	IL	V _{IN(A, B, C, and e} under test =	enable) 0.6 V	Full	0.02	-1	1	-1	1	
Input Current, V _{IN} High	I _H	V _{IN(A, B, C, and enable)} under test = 1.4 V		Full	0.02	-1	1	-1	1	μA
Dynamic Characterist	ics									
T						-	-	-	-	
Transition Time	t _{TRANS}	$R_L = 300 \ \Omega, \ C_L = 35 \ pF$ see Fig. 1, 2, 3		Full	-	-	-	-	-	
5 11 T O T				Room	130	-	-	-	-	
Enable Turn-On Time	t _{ON}			Full	-	-	-	-	-	
Frankla Truss Off Times				Room	78	-	-	-	-	n
Enable Turn-Off Time	t _{OFF}			Full	-	-	-	-	-	
Break-Before-Make					130	-	-	-	-	
Time Delay	t _D			Full	-	-	-	-	-	
Charge Injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega,$	C _L = 1 nF	Room	0.34	-	-	-	-	р(
Off Isolation e	OIRR	D 50.0.0	1	Room	-88	-	-	-	-	
Channel-to-Channel Crosstalk ^e	X _{TALK}	$R_L = 50 \Omega, C_L$ f = 100 kH	= i pr Iz	Room	-105	-	-	-	-	dE
			DG4051E	Room	2.6	-	-	-	-	
Source Off Capacitance e	C _{S(off)}	f = 1 MHz	DG4052E	Room	2.6	-	-	-	-	
Capacitarice			DG4053E	Room	2.5	-	-	-	-	
			DG4051E	Room	10.7	-	-	-	-	
Drain Off Capacitance e	C _{D(off)}	f = 1 MHz	DG4052E	Room	5.7	-	-	-	-	pl
			DG4053E	Room	3.6	-	-	-	-	
<u> </u>			DG4051E	Room	16.4	-	-	-	-	
Channel On Capacitance ^e	C _{D(on)}	f = 1 MHz	DG4052E	Room	10.9	-	-	-	-	
Capacitarice			DG4053E	Room	9.1	-	-	-	-	
Power Supplies										
Power Supply Current	l+			Room	0.05	-	1	-	1	
- ower Supply Current	1+			Full		-	10	-	10	
Negative Supply	I-	V	- 0 V or 3 V	Room	-0.05	-1	-	-1	-	.,,
Current	1-	V _{IN} (A, B, C, and enable) ⁻	- U V UI 3 V	Full	_	-10	-	-10	-	μA
Ground Current	1-			Room	-0.05	-1	-	-1		
GIOUIIU OUITEIIL	I _{GND}			Full	-	-10	-	-10	-	

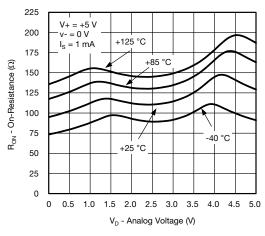
- a. V_{IN} = input voltage to perform proper function. b. Room = 25 °C, full = as determined by the operating temperature suffix. c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- e. Guaranteed by design, not subject to production test.

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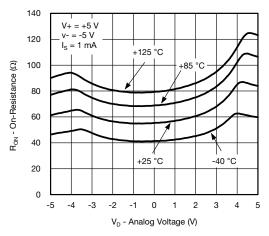
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



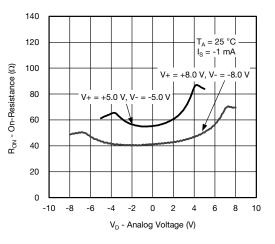
On-Resistance vs. Analog Voltage (Single Supply)



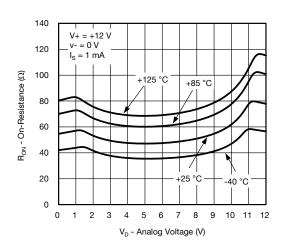
On-Resistance vs. Analog Voltage (Temperature)



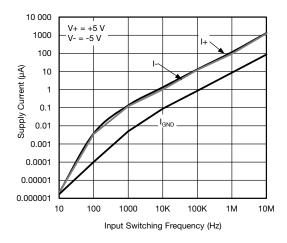
On-Resistance vs. Analog Voltage (Temperature)



On-Resistance vs. Analog Voltage (Dual Supply)



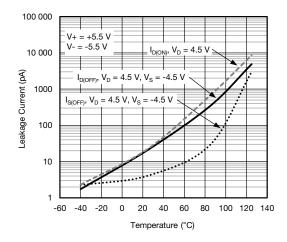
On-Resistance vs. Analog Voltage (Temperature)



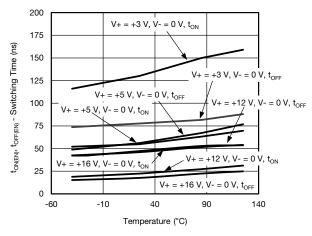
Supply Current vs. Input Switching Frequency

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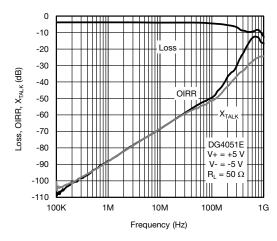
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



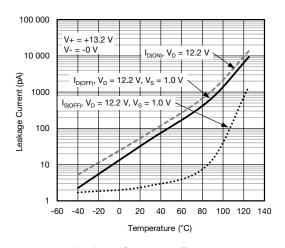
Leakage Current vs. Temperature



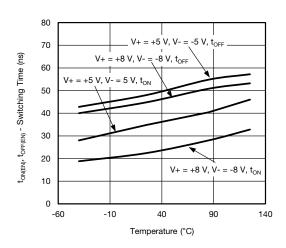
Switching Time vs. Temperature (Single Supply)



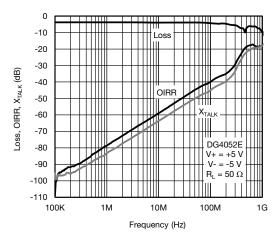
DG4051E Insertion Loss, Off-Isolation, Crosstalk vs. Frequency



Leakage Current vs. Temperature

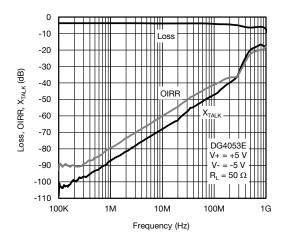


Switching Time vs. Temperature (Dual Supply)

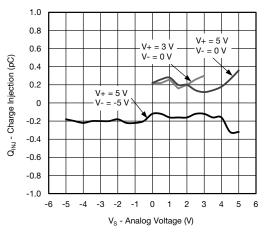


DG4052E Insertion Loss, Off-Isolation, Crosstalk vs. Frequency

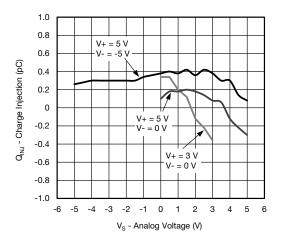
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



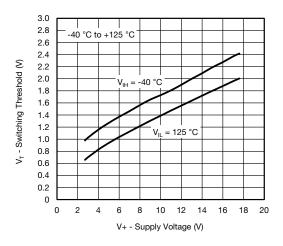
DG4053E Insertion Loss, Off-Isolation, Crosstalk vs. Frequency



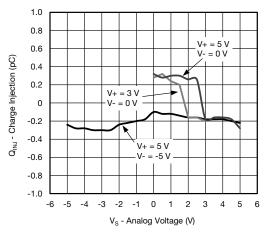
DG4051E Charge Injection vs. Analog Voltage



DG4052E Charge Injection vs. Analog Voltage



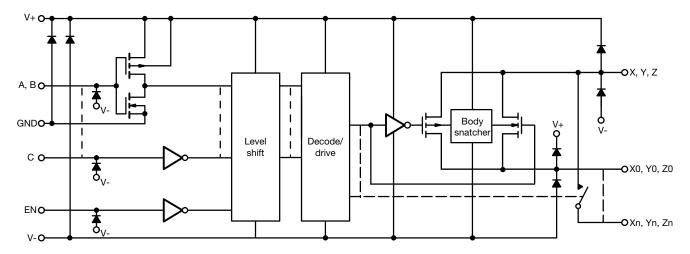
Switching Threshold vs. V+ Supply Voltage



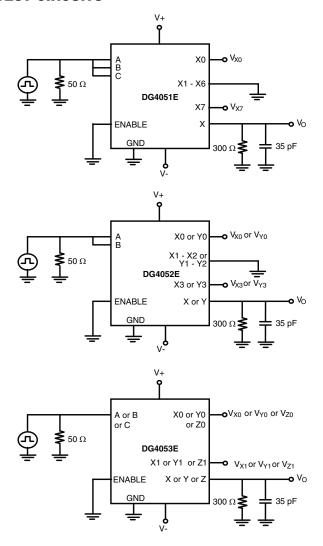
DG4053E Charge Injection vs. Analog Voltage

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SCHEMATIC DIAGRAM (Typical Channel)



TEST CIRCUITS



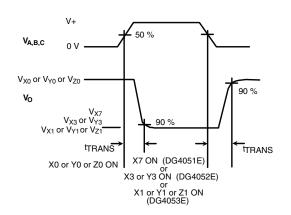
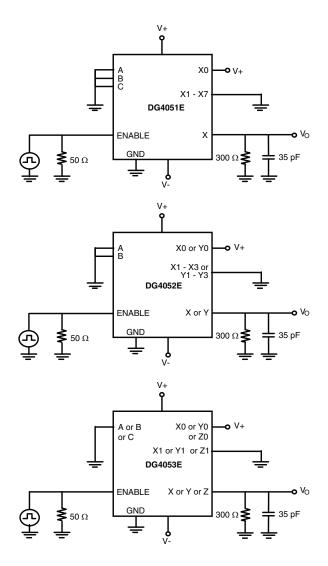


Fig. 1 - Transition Time

TEST CIRCUITS



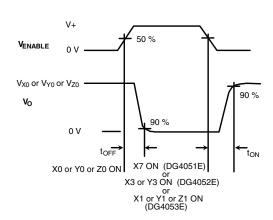


Fig. 2 - Enable Switching Time

TEST CIRCUITS

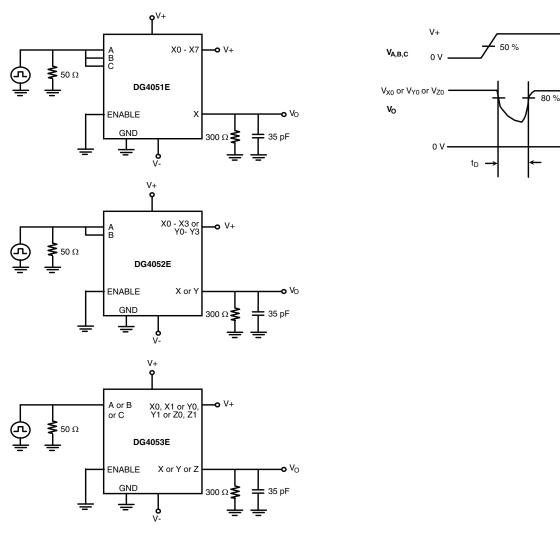


Fig. 3 - Break-Before-Make

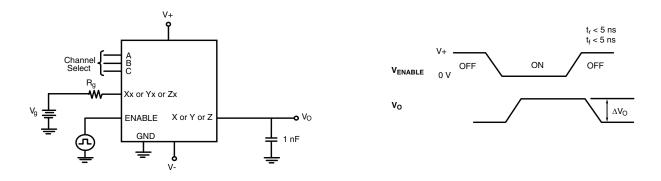


Fig. 4 - Charge Injection



TEST CIRCUITS

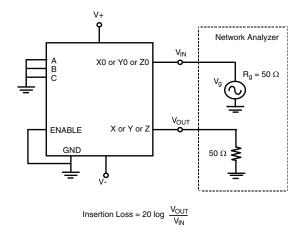


Fig. 5 - Insertion Loss

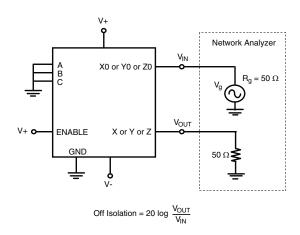


Fig. 7 - Off Isolation

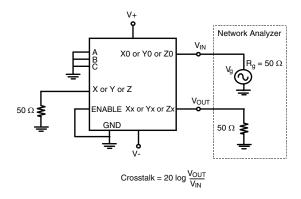


Fig. 6 - Crosstalk

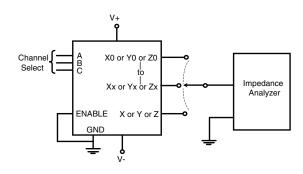
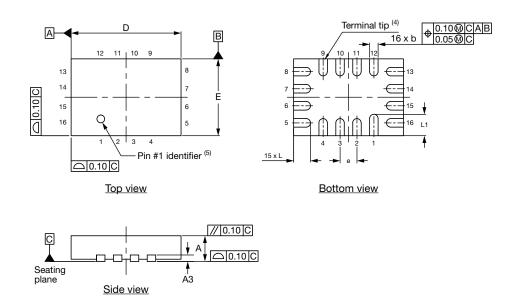


Fig. 8 - Source, Drain Capacitance

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Thin miniQFN16 Case Outline



DIMENSIONS		MILLIMETERS (1)			INCHES		
DIMENSIONS	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.50	0.55	0.60	0.020	0.022	0.024	
A1	0	-	0.05	0	-	0.002	
A3		0.15 ref.					
b	0.15	0.20	0.25	0.006	0.008	0.010	
D	2.50	2.60	2.70	0.098	0.102	0.106	
е		0.40 BSC		0.016 BSC			
Е	1.70	1.80	1.90	0.067	0.071	0.075	
L	0.35	0.40	0.45	0.014	0.016	0.018	
L1	0.45	0.50	0.55	0.018	0.020	0.022	
N (3)	16			16			
Nd ⁽³⁾		4 4					
Ne ⁽³⁾		4		4			

Notes

- (1) Use millimeters as the primary measurement.
- (2) Dimensioning and tolerances conform to ASME Y14.5M. 1994.
- (3) N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.
- (4) Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.
- (5) The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.
- (6) Package warpage max. 0.05 mm.

ECN: T16-0226-Rev. B, 09-May-16

DWG: 6023



SOIC (NARROW): 16-LEAD JEDEC Part Number: MS-012



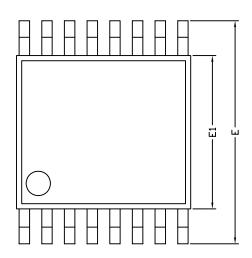
	MILLIM	IETERS	INC	HES						
Dim	Min	Max	Min	Max						
Α	1.35	1.75	0.053	0.069						
A ₁	0.10	0.20	0.004	0.008						
В	0.38	0.51	0.015	0.020						
С	0.18	0.23	0.007	0.009						
D	9.80	10.00	0.385	0.393						
Е	3.80	4.00	0.149	0.157						
е	1.27	BSC	0.050	BSC						
Н	5.80	6.20	0.228	0.244						
L	0.50	0.93	0.020	0.037						
0	0°	8°	0°	8°						
ECN: S-0	ECN: S-03946—Rev. F. 09-Jul-01									

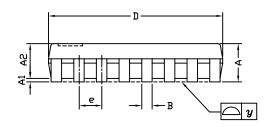
DWG: 5300





TSSOP: 16-LEAD







	DIMENSIONS IN MILLIMETERS						
Symbols	Min	Nom	Max				
A	-	1.10	1.20				
A1	0.05	0.10	0.15				
A2	-	1.00	1.05				
В	0.22	0.28	0.38				
С	-	0.127	-				
D	4.90	5.00	5.10				
E	6.10	6.40	6.70				
E1	4.30	4.40	4.50				
е	-	0.65	-				
L	0.50	0.60	0.70				
L1	0.90	1.00	1.10				
у	-	-	0.10				
θ1	0°	3°	6°				
ECN: S-61920-Rev D 23	R-Oct-06						

ECN: S-61920-Rev. D, 23-Oct-06

DWG: 5624

Document Number: 74417 www.vishay.com 23-Oct-06 1



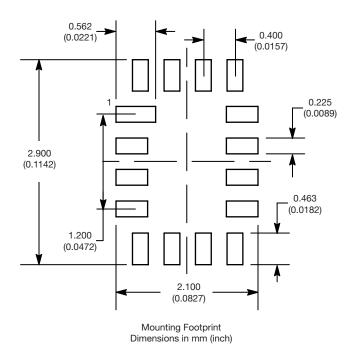
RECOMMENDED MINIMUM PAD FOR TSSOP-16



Recommended Minimum Pads Dimensions in inches (mm)

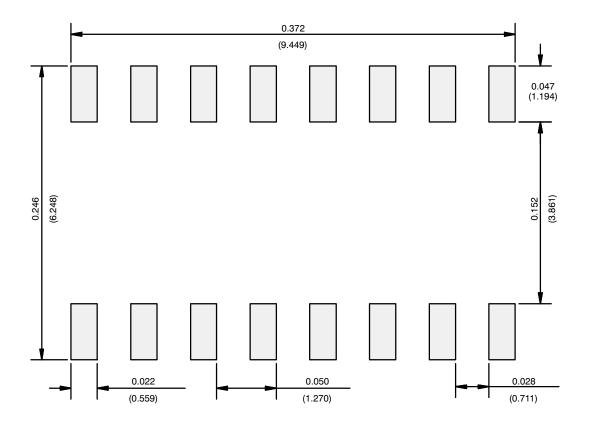


RECOMMENDED MINIMUM PADS FOR MINI QFN 16L





RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

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